

SANYO

No.3165

2SK1236

N-Channel GaAs MES FET

12GHz-Band Local Oscillator,
Amplifier Applications**Features**

- Ceramic package
- Adoption of high reliable protection film

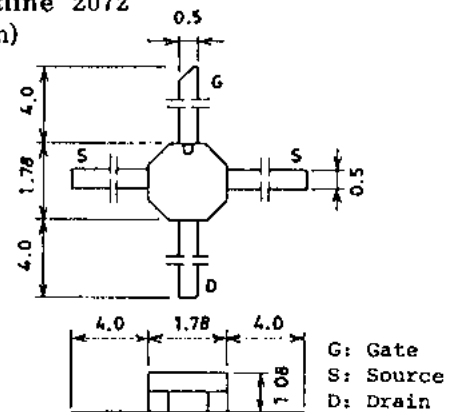
Absolute Maximum Ratings at Ta = 25°C

			unit
Drain to Source Voltage	V_{DS}	6	V
Gate to Source Voltage	V_{GS}	-5	V
Drain Current	I_D	100	mA
Allowable Power Dissipation	P_D	300	mW
Junction Temperature	T_j	150	°C
Storage Temperature	T_{stg}	-65 to +150	°C

Electrical Characteristics at Ta = 25°C

		min	typ	max	unit
Gate to Drain Breakdown Voltage	$V_{(BR)GDS}$ $I_G = -10\mu A, V_{DS} = 0V$	-5			V
Gate Cutoff Current	I_{GSS} $V_{GS} = -3V, V_{DS} = 0V$			-10	μA
Drain Current	I_{DSS} $V_{DS} = 3V, V_{GS} = 0V$	20		90	mA
Gate to Source Cutoff Voltage	$V_{GS(off)}$ $V_{DS} = 3V, I_D = 100\mu A$	-0.5		-5	V
Forward Transfer Admittance	$ y_{fs} $ $V_{DS} = 3V, I_D = 10mA$	20	40		mS
Noise Figure	NF $V_{DS} = 3V, I_D = 10mA, f = 12GHz$		2	2.8	dB
Associated Gain	Ga $V_{DS} = 3V, I_D = 10mA, f = 12GHz$	5.3	6.3		dB
Maximum Available Power Gain	MAG $V_{DS} = 3V, I_D = 30mA, f = 12GHz$		7		dB
Maximum Oscillation Frequency	f_{max} $V_{DS} = 3V, I_D = 30mA$		50		GHz

The application circuit diagrams and circuit constants herein are included as an example and provide no guarantee for designing equipment to be mass-produced. The information herein is believed to be accurate and reliable. However, no responsibility is assumed by SANYO for its use; nor for any infringements of patents or other rights of third parties which may result from its use.

Case Outline 2072
(unit: mm)

Specifications and information herein are subject to change without notice.

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